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Author: Haiting Xie Qi Wu Ling Xu Lei Zhang Guochao Liu Chengyuan Dong



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Haiting Xie, Qi Wu, Ling Xu, Lei Zhang, Guochao Liu, and Chengyuan Dong*

National Engineering Lab for TFT-LCD Materials and Technologies, Department of Electronic Engineering, Shanghai Jiao Tong University, Shanghai, 200240, China

Corresponding author. Tel.: +86 21 34207894; fax: +86 21 34204371.

E-mail address: cydong@sjtu.edu.cn (C. Dong).

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